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Key indicators

Single-crystal X-ray study

$T = 293\text{ K}$

Mean $\sigma(\text{Si}-\text{O}) = 0.006\text{ \AA}$

Disorder in main residue

R factor = 0.025

wR factor = 0.064

Data-to-parameter ratio = 12.8

For details of how these key indicators were automatically derived from the article, see <http://journals.iucr.org/e>.

Dieuropium(III) silicodimonophosphatediphosphate

A new europium(III) silicophosphate, whose formula may be considered to be $\text{Eu}_2\text{Si}(\text{PO}_4)_2(\text{P}_2\text{O}_7)$, has been found to consist of phosphosilicate chains with $\text{Si}-\text{O}-\text{P}-\text{O}-\text{P}-\text{O}-\text{Si}$ backbones extending in the a direction. The P_2O_7 group and the Si atom both lie on crystallographic twofold axes. Tetrahedral silicon is further bound to two monophosphate groups. This is a silicophosphate of previously unseen type.

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Comment

The structural literature contains reports of only three silicophosphate materials with +3 charged cations. These contain two distinctly different silicophosphate moieties.

$\text{RuSiP}_3\text{O}_{11}$ (Fukuoka *et al.*, 1996) may be seen to exist with Si_2O_7 groups sharing each of its six terminal O atoms with a different P_2O_7 group. Each P_2O_7 group is seen to share a single O atom per PO_4 tetrahedron with an Si_2O_7 group, creating a three-dimensional network of linked tetrahedra which encapsulate Ru^{3+} cations. $\text{MoSiP}_3\text{O}_{11}$ (Leclaire & Raveau, 1987) shows the same motif, with Mo^{3+} encapsulated within the three-dimensional network of silicophosphates.

$\text{Mo}_3\text{SiP}_5\text{O}_{19}$ (Wang *et al.*, 1988) exists with isolated $(\text{PO}_3\text{O})_3\text{SiOSi}(\text{OPO}_3)_3$ and $(\text{PO}_3\text{O})_3\text{POP}(\text{OPO}_3)_3$ units stacked in columns parallel to the hexagonal c axis. $\text{V}_3\text{SiP}_5\text{O}_{19}$ (Leclaire *et al.*, 1986) appears to be isostructural with the molybdenum-containing compound of similar formula. $\text{Mo}_4\text{Si}_2\text{P}_6\text{O}_{25}$ (Leclaire *et al.*, 1988) shows a similar motif but with $(\text{PO}_3\text{O})_3\text{SiOSi}(\text{OPO}_3)_3$ groups only.

$\text{Eu}_2\text{Si}(\text{PO}_4)_2(\text{P}_2\text{O}_7)$ crystallizes with silicophosphate chains with $\text{Si}-\text{O}-\text{P}-\text{O}-\text{P}-\text{O}$ backbones extending in the a direction (Fig. 1). Tetrahedral silicon is further bound to two monophosphate groups, whereas the P atoms of the polymeric chain are further bonded to two terminal O atoms, O21 and O23 (Fig. 1). Thus, it is a silicophosphate of a previously unseen type.

Atoms O21, O22 and O23 display a 0.46/0.54 disorder with positions O21', O22' and O23', and are related to them by a 23.3° rotation about the $\text{P2}-\text{O24}$ bond. Atoms O22 and O22' lie on a twofold axis.

Eu atoms are localized between PO_3 groups and the two terminal O atoms of a P atom of the polymeric chain. Eu is within bonding distance of each of the disordered positions, O21, O21', O23 and O23'. Eu^{3+} is six coordinate [average $\text{Eu}-\text{O}$ 2.317 (6) \AA], with a seventh $\text{Eu}-\text{O}$ distance of 2.544 (5) \AA . With the inclusion of the seventh distance, the geometry at europium appears to be that of a pentagonal bipyramid. Using bond-valence calculations to ascertain the validity of the

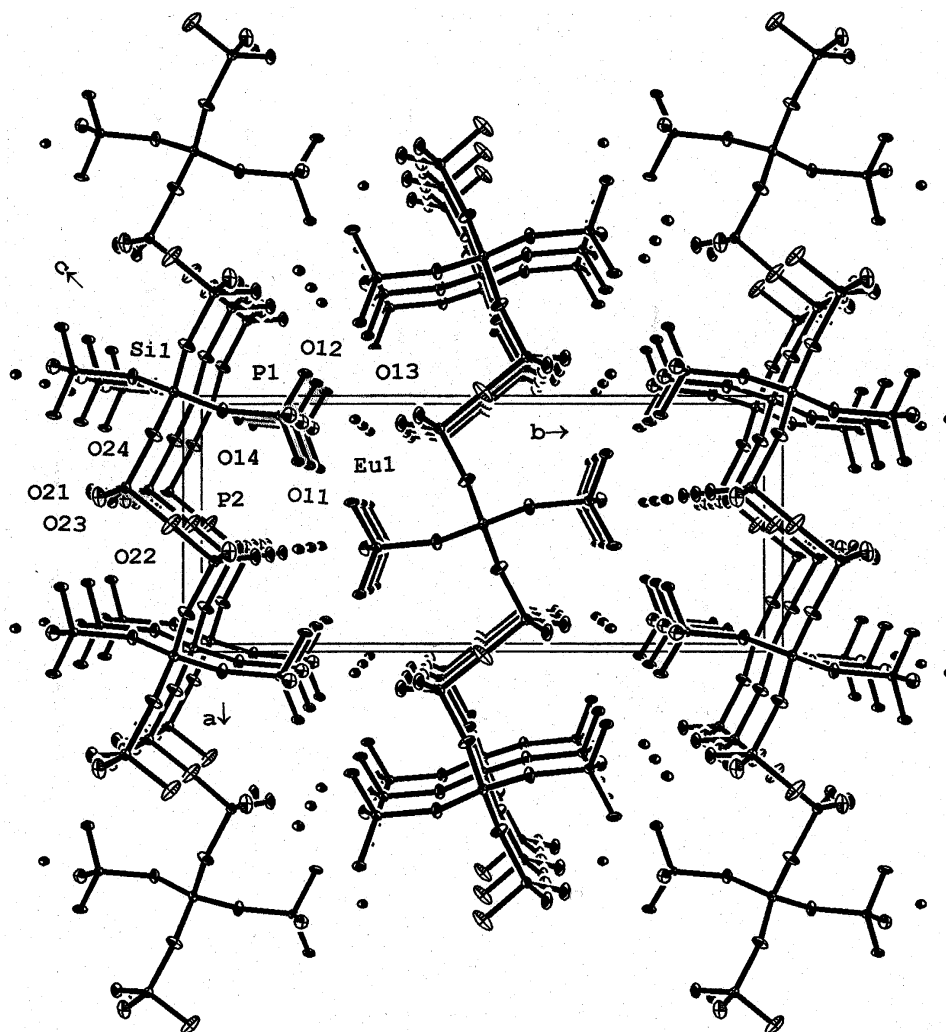


Figure 1

View of dieuropium(III) silicodimonophosphatediphosphate projected on the *ab* plane. Displacement ellipsoids are shown at the 50% probability level.

seventh distance (Brown, 1981) leads to a valence bond total of 3.065 using the six Eu—O distances of less than 2.451 (5) Å, but a significantly larger total of 3.352 Å if the seventh distance is included. Both geometry and valence-bond calculations argue that this longer distance is meaningful.

Silicon displays tetrahedral geometry, with an average Si—O distance of 1.604 (6) Å. Phosphorus tetrahedra have average P—O distances of 1.511 (11) Å.

Experimental

Crystal data

$\text{Eu}_2\text{Si}(\text{PO}_4)_2(\text{P}_2\text{O}_7)$
 $M_r = 695.90$
 Orthorhombic, $P2_12_12$
 $a = 7.056$ (1) Å
 $b = 16.376$ (3) Å
 $c = 5.585$ (1) Å
 $V = 645.34$ (19) Å³
 $Z = 2$
 $D_x = 3.581$ Mg m⁻³

Mo $K\alpha$ radiation
 Cell parameters from 24 reflections
 $\theta = 5.6$ – 16.9°
 $\mu = 10.30$ mm⁻¹
 $T = 293$ (2) K
 Needle, colorless
 $0.15 \times 0.12 \times 0.10$ mm

Data collection

Syntax P4 four-circle diffractometer
 $\theta/2\theta$ scans
 Absorption correction: ψ scan
 (XEMP; Siemens, 1990)
 $T_{\min} = 0.181$, $T_{\max} = 0.357$
 1578 measured reflections
 1422 independent reflections
 1388 reflections with $I > 2\sigma(I)$

$R_{\text{int}} = 0.031$
 $\theta_{\text{max}} = 30.0^\circ$
 $h = -1 \rightarrow 9$
 $k = -1 \rightarrow 23$
 $l = -1 \rightarrow 7$
 3 standard reflections
 every 97 reflections
 intensity decay: none

Refinement

Refinement on F^2
 $R[F^2 > 2\sigma(F^2)] = 0.025$
 $wR(F^2) = 0.064$
 $S = 1.07$
 1422 reflections
 111 parameters

$w = 1/[\sigma^2(F_o^2) + (0.0334P)^2 + 1.2737P]$
 where $P = (F_o^2 + 2F_c^2)/3$
 $(\Delta/\sigma)_{\text{max}} = 0.012$
 $\Delta\rho_{\text{max}} = 0.01$ e Å⁻³
 $\Delta\rho_{\text{min}} = -0.02$ e Å⁻³
 Extinction correction: SHELXL97
 Extinction coefficient: 0.0030 (4)

Table 1
Selected geometric parameters (Å, °).

Eu1—O21 ⁱ	2.217 (18)	Si1—O13	1.615 (5)
Eu1—O21 ^{ri}	2.344 (13)	P1—O11	1.514 (5)
Eu1—O23 ⁱⁱ	2.309 (15)	P1—O12	1.523 (5)
Eu1—O23 ⁱⁱⁱ	2.240 (12)	P1—O13	1.577 (5)
Eu1—O14 ⁱⁱⁱⁱ	2.267 (5)	P1—O14	1.504 (5)
Eu1—O12 ^{iv}	2.349 (4)	P2—O21	1.476 (18)
Eu1—O11 ^v	2.360 (4)	P2—O21'	1.496 (15)
Eu1—O12	2.451 (5)	P2—O22	1.536 (5)
Eu1—O11	2.544 (5)	P2—O22'	1.547 (5)
Si1—O24	1.593 (6)	P2—O23	1.520 (14)
Si1—O24 ^{vi}	1.593 (6)	P2—O23'	1.436 (12)
Si1—O13 ^{vi}	1.615 (5)	P2—O24	1.568 (5)
O21 ⁱ —Eu1—O14 ⁱⁱⁱⁱ	82.2 (5)	O21 ^{ri} —Eu1—O11	149.4 (4)
O23 ⁱⁱ —Eu1—O14 ⁱⁱⁱⁱ	169.9 (4)	O12—Eu1—O11	57.32 (14)
O21 ⁱ —Eu1—O23 ⁱⁱ	87.6 (5)	O24—Si1—O24 ^{vi}	103.6 (5)
O14 ⁱⁱⁱⁱ —Eu1—O23 ⁱⁱ	169.7 (4)	O24—Si1—O13 ^{vi}	112.5 (3)
O21 ⁱ —Eu1—O12 ^{iv}	78.4 (5)	O24 ^{vi} —Si1—O13 ^{vi}	111.4 (3)
O23 ⁱⁱ —Eu1—O12 ^{iv}	82.1 (4)	O24—Si1—O13	111.4 (3)
O14 ⁱⁱⁱⁱ —Eu1—O12 ^{iv}	88.8 (2)	O24 ^{vi} —Si1—O13	112.5 (3)
O23 ⁱⁱ —Eu1—O12 ^{iv}	88.0 (5)	O13 ^{vi} —Si1—O13	105.6 (4)
O21 ⁱ —Eu1—O11 ^v	87.9 (5)	O14—P1—O11	115.4 (3)
O23 ⁱⁱ —Eu1—O11 ^v	96.4 (4)	O14—P1—O12	114.6 (3)
O14 ⁱⁱⁱⁱ —Eu1—O11 ^v	93.5 (2)	O11—P1—O12	104.2 (3)
O23 ⁱⁱ —Eu1—O11 ^v	87.4 (5)	O14—P1—O13	107.8 (3)
O12 ^{iv} —Eu1—O11 ^v	165.72 (15)	O11—P1—O13	107.5 (3)
O14 ⁱⁱⁱⁱ —Eu1—O21 ^{ri}	95.7 (4)	O12—P1—O13	106.8 (3)
O12 ^{iv} —Eu1—O21 ^{ri}	83.9 (4)	O21—P2—O23	116.4 (8)
O11 ^v —Eu1—O21 ^{ri}	81.9 (4)	O21—P2—O22	108.9 (10)
O21 ⁱ —Eu1—O12	156.9 (5)	O23—P2—O22	108.8 (11)
O23 ⁱⁱ —Eu1—O12	83.2 (4)	O21—P2—O24	110.7 (8)
O14 ⁱⁱⁱⁱ —Eu1—O12	98.71 (18)	O23—P2—O24	109.6 (8)
O23 ⁱⁱ —Eu1—O12	91.1 (4)	O22—P2—O24	101.5 (2)
O12 ^{iv} —Eu1—O12	124.68 (12)	O23'—P2—O22'	109.0 (9)
O11 ^v —Eu1—O12	68.94 (15)	O21'—P2—O22'	109.7 (9)
O21 ^{ri} —Eu1—O12	148.0 (4)	O23'—P2—O24	108.4 (6)
O21 ⁱ —Eu1—O11	145.8 (5)	O23'—P2—O21'	118.1 (7)
O23 ⁱⁱ —Eu1—O11	78.3 (4)	O21'—P2—O24	108.4 (6)
O14 ⁱⁱⁱⁱ —Eu1—O11	94.34 (18)	O22'—P2—O24	102.2 (2)
O23 ⁱⁱ —Eu1—O11	93.4 (4)	P2 ^{vii} —O22—P2	158 (2)
O12 ^{iv} —Eu1—O11	67.52 (15)	P2—O22'—P2 ^{vii}	154.1 (16)
O11 ^v —Eu1—O11	126.26 (12)		

Symmetry codes: (i) $\frac{1}{2} - x, \frac{1}{2} + y, 2 - z$; (ii) $\frac{1}{2} - x, \frac{1}{2} + y, 3 - z$; (iii) $x, y, z - 1$; (iv) $\frac{1}{2} + x, \frac{1}{2} - y, 2 - z$; (v) $x - \frac{1}{2}, \frac{1}{2} - y, 2 - z$; (vi) $-x, -y, z$; (vii) $1 - x, -y, z$.

The orthorhombic cell displayed absences $h00$, $h = 2n$ and $0k0$, $k = 2n$, fixing the space group as $P2_12_12$. Disorder of three O atoms became apparent as refinement progressed. The P_2O_7 group exists with a twofold axis passing through the bridging O atom, which was seen to exist in two positions O22 and O22', both on the twofold axis.

While P2 and O24 were seen in ordered positions, alternate or disordered positions were seen for terminal O atoms O21 (O21') and O23 (O23'). O21, O22, O23 and O24 form a tetrahedral array about P2 as do O21', O22', O23' and O24. The disorder may be understood in terms of an approximately 22° rotation about the P2—O24 (and the P2a—O24a bond related by the twofold axis) corresponding to the bridging O atom being 'up' or 'down' and resulting in a 0.59 Å displacement of each of the disordered atoms. O21 and O23 were refined with an occupancy parameter equal to x (O22 occupancy = $0.5x$) whereas O21' and O23' were refined with an occupancy parameter of $1 - x$ [O22' occupancy = $(1 - x)/2$]. The refined value of x is 0.46 (3). Anisotropic displacement parameters for pairs of close atoms (O21/O21', O22/O22' and O23/O23') were constrained to identical values for each pair. The identity of the Si atom was confirmed by observing that the occupancy parameter refined to the correct value (0.5), confirming the electron density of the position, by comparing the Si—O distances with those of the literature and by observing the charge neutrality of the structure which requires a +4 cation in that position.

Data collection: XSCANS (Siemens, 1991); cell refinement: XSCANS; data reduction: XSCANS; program(s) used to solve structure: SHELXS97 (Sheldrick, 1990); program(s) used to refine structure: SHELXL97 (Sheldrick, 1997); molecular graphics: XP (Siemens, 1990); software used to prepare material for publication: SHELXL97.

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supporting information

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S1. Comment

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$\text{RuSiP}_3\text{O}_{11}$ (Fukuoka *et al.*, 1996) may be seen to exist with Si_2O_7 groups sharing each of its six terminal O atoms with a different P_2O_7 group. Each P_2O_7 group is seen to share a single O atom per PO_4 tetrahedron, with an Si_2O_7 group creating a three-dimensional network of linked tetrahedra which encapsulate Ru^{+3} cations. $\text{MoSiP}_3\text{O}_{11}$ (Leclaire & Raveau, 1987) shows the same motif, with Mo^{+3} encapsulated within the three-dimensional network of silicophosphates.

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Atoms O21, O22 and O23 display a 0.455/0.545 disorder with positions O21', O22' and O23', and are related to them by a 23.3° rotation about the P2—O24 bond (Fig. 2). Atom O22 and O22' lie on a twofold axis.

Eu atoms are localized between PO_3 groups and the two terminal O atoms of a P atom of the polymeric chain. Eu is within bonding distance of each of the disordered positions, O21, O21', O23 and O23'. Eu^{III} is six coordinate [average Eu—O 2.317 (6) Å], with a seventh Eu—O distance of 2.544 (5) Å. With the inclusion of the seventh distance, the geometry at europium appears to be that of a pentagonal bipyramid. Using bond-valence calculations to ascertain the validity of the seventh distance (Brown, 1981) leads to a valence bond total of 3.065 using the six Eu—O distances of less than 2.451 (5) Å, but a significantly larger total of 3.352 Å if the seventh distance is included. Both geometry and valence-bond calculations argue that this longer distance is meaningful.

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S2. Refinement

The orthorhombic cell displayed absences $h00$, $h = 2n$ and $0k0$, $k = 2n$, fixing the space group as $P2_12_12$. Disorder of three O atoms became apparent as refinement progressed. The P_2O_7 group exists with a twofold axis passing through the bridging O atom, which was seen to exist in two positions O22 and O22', both on the twofold axis. While P2 and O24 were seen in ordered positions, alternate or disordered positions were seen for terminal O atoms O21 (O21') and O23 (O23'). O21, O22, O23 and O24 form a tetrahedral array about P2 as do O21', O22' O23' and O24. The disorder may be

understood in terms of an approximately 22° rotation about the P2—O24 (and the P2a—O24a bond related by the twofold axis) corresponding to the bridging O atom being 'up' or 'down' and resulting in a 0.59 Å displacement of each of the disordered atoms. O21 and O23 were refined with an occupancy parameter equal to x (O22 occupancy = $0.5x$) whereas O21' and O23' were refined with an occupancy parameter of $1 - x$ [O22' occupancy = $(1 - x)/2$]. The refined value of x is 0.46 (3). Anisotropic displacement parameters for pairs of close atoms (O21/O21', O22/O22' and O23/O23') were constrained to identical values for each pair. The identity of the Si atom was confirmed by observing that the occupancy parameter refined to the correct value (1/2), confirming the electron density of the position, by comparing the Si—O distances with those of the literature and by observing the charge neutrality of the structure which requires a +4 cation in that position.

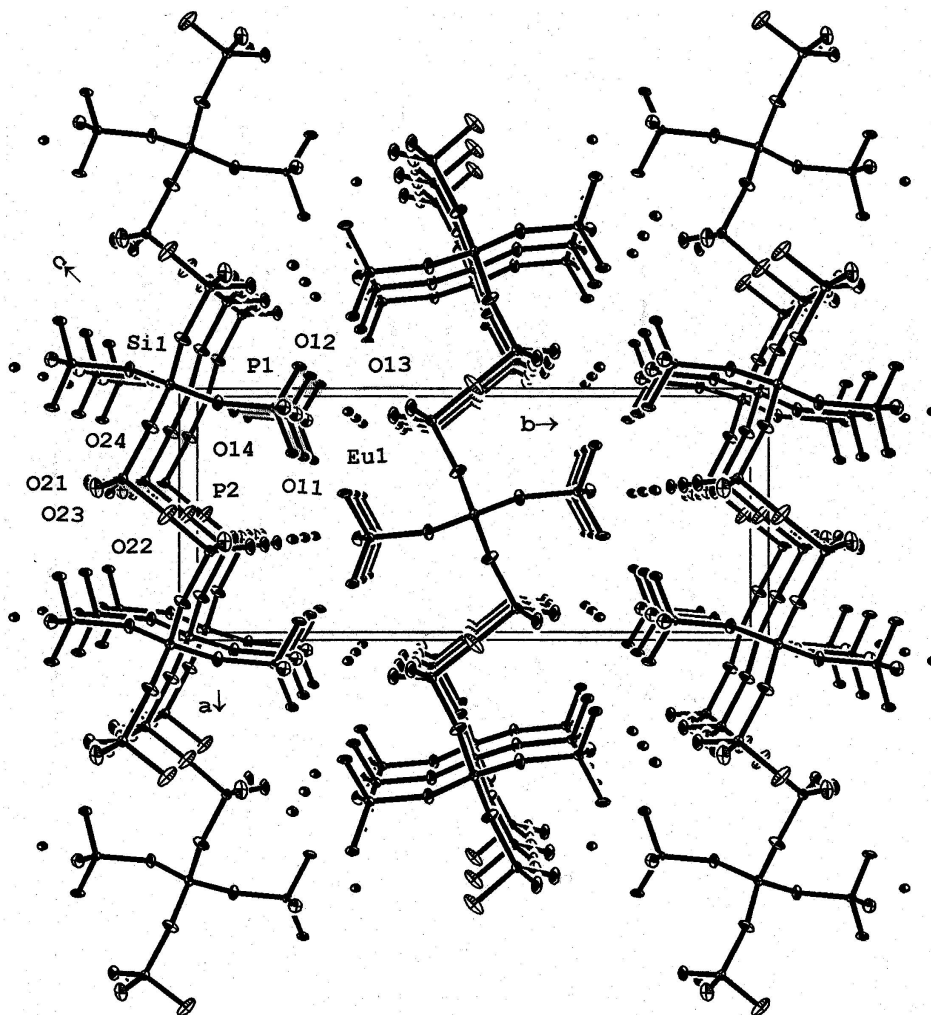


Figure 1

View of dieuropium(III) silicodimonophosphatediphosphate projected on the ab plane. Displacement ellipsoids are shown at the 50% probability level.

Diuropium(III) silicodimonophosphatediphosphate

Crystal data

Eu₂Si(PO₄)₂(P₂O₇)
M_r = 695.90
 Orthorhombic, *P*2₁2₁2
a = 7.056 (1) Å
b = 16.376 (3) Å
c = 5.585 (1) Å
V = 645.34 (19) Å³
Z = 2
F(000) = 640

D_x = 3.581 Mg m⁻³
 Mo *K*α radiation, λ = 0.71073 Å
 Cell parameters from 24 reflections
 θ = 5.6–16.9°
 μ = 10.30 mm⁻¹
T = 293 K
 Needle, colorless
 0.15 × 0.12 × 0.1 mm

Data collection

Syntex P4 four-circle
 diffractometer
 Radiation source: fine-focus sealed tube
 Graphite monochromator
 θ/2θ scans
 Absorption correction: ψ scan
 (*XEMP*; Siemens, 1990)
T_{min} = 0.181, *T_{max}* = 0.357
 1578 measured reflections

1422 independent reflections
 1388 reflections with *I* > 2σ(*I*)
R_{int} = 0.031
 θ_{max} = 30.0°, θ_{min} = 2.5°
h = -1→9
k = -1→23
l = -1→7
 3 standard reflections every 97 reflections
 intensity decay: 0.0%

Refinement

Refinement on *F*²
 Least-squares matrix: full
R[*F*² > 2σ(*F*²)] = 0.025
wR(*F*²) = 0.064
S = 1.07
 1422 reflections
 111 parameters
 1 restraint
 Primary atom site location: structure-invariant
 direct methods

Secondary atom site location: difference Fourier
 map
w = 1/[σ²(*F_o*²) + (0.0334*P*)² + 1.2737*P*]
 where *P* = (*F_o*² + 2*F_c*²)/3
 (Δ/σ)_{max} = 0.012
 Δρ_{max} = 0.01 e Å⁻³
 Δρ_{min} = -0.02 e Å⁻³
 Extinction correction: *SHELXL97*,
*F_c** = *kF_c*[1 + 0.001*xF_c*²λ³/sin(2θ)]^{-1/4}
 Extinction coefficient: 0.0030 (4)

Special details

Geometry. All e.s.d.'s (except the e.s.d. in the dihedral angle between two l.s. planes) are estimated using the full covariance matrix. The cell e.s.d.'s are taken into account individually in the estimation of e.s.d.'s in distances, angles and torsion angles; correlations between e.s.d.'s in cell parameters are only used when they are defined by crystal symmetry. An approximate (isotropic) treatment of cell e.s.d.'s is used for estimating e.s.d.'s involving l.s. planes.

Refinement. Refinement of *F*² against ALL reflections. The weighted *R*-factor *wR* and goodness of fit *S* are based on *F*², conventional *R*-factors *R* are based on *F*, with *F* set to zero for negative *F*². The threshold expression of *F*² > σ(*F*²) is used only for calculating *R*-factors(gt) etc. and is not relevant to the choice of reflections for refinement. *R*-factors based on *F*² are statistically about twice as large as those based on *F*, and *R*-factors based on ALL data will be even larger.

Fractional atomic coordinates and isotropic or equivalent isotropic displacement parameters (Å²)

	<i>x</i>	<i>y</i>	<i>z</i>	<i>U_{iso}</i> */ <i>U_{eq}</i>	Occ. (<1)
Eu1	0.08893 (4)	0.284646 (19)	0.86217 (6)	0.01108 (10)	
Si1	0.0000	0.0000	1.4557 (5)	0.0133 (5)	
P1	0.0855 (2)	0.16894 (9)	1.3063 (3)	0.0112 (3)	
O11	0.2587 (6)	0.1945 (3)	1.1648 (10)	0.0167 (10)	

O12	-0.0798 (6)	0.2069 (3)	1.1706 (9)	0.0188 (10)	
O13	0.0651 (8)	0.0734 (3)	1.2809 (9)	0.0190 (10)	
O14	0.0910 (9)	0.1889 (3)	1.5690 (9)	0.0216 (10)	
P2	0.3633 (2)	-0.07078 (10)	1.6411 (4)	0.0134 (3)	
O21	0.378 (3)	-0.1316 (9)	1.447 (4)	0.025 (2)	0.455 (12)
O21'	0.407 (2)	-0.1026 (7)	1.396 (3)	0.025 (2)	0.545 (12)
O22	0.5000	0.0000	1.589 (5)	0.039 (3)	0.455 (12)
O22'	0.5000	0.0000	1.703 (4)	0.039 (3)	0.545 (12)
O23	0.400 (3)	-0.1017 (9)	1.893 (3)	0.026 (2)	0.455 (12)
O23'	0.361 (2)	-0.1278 (8)	1.836 (2)	0.026 (2)	0.545 (12)
O24	0.1666 (7)	-0.0263 (3)	1.6321 (11)	0.0244 (11)	

Atomic displacement parameters (Å²)

	U^{11}	U^{22}	U^{33}	U^{12}	U^{13}	U^{23}
Eu1	0.00969 (13)	0.01415 (14)	0.00939 (14)	-0.00079 (12)	-0.00027 (12)	0.00019 (13)
Si1	0.0139 (11)	0.0104 (10)	0.0155 (12)	0.0008 (9)	0.000	0.000
P1	0.0109 (6)	0.0115 (6)	0.0110 (7)	-0.0013 (6)	-0.0004 (6)	0.0010 (5)
O11	0.0101 (18)	0.021 (2)	0.019 (2)	0.0008 (16)	-0.002 (2)	0.0089 (19)
O12	0.0083 (17)	0.025 (2)	0.023 (2)	0.002 (2)	-0.002 (2)	0.008 (2)
O13	0.028 (3)	0.0118 (19)	0.017 (2)	-0.0018 (19)	0.006 (2)	-0.0021 (18)
O14	0.025 (2)	0.024 (2)	0.016 (2)	0.000 (2)	0.000 (3)	-0.005 (2)
P2	0.0131 (7)	0.0120 (6)	0.0150 (7)	-0.0005 (5)	-0.0008 (7)	-0.0005 (7)
O21	0.032 (5)	0.013 (6)	0.030 (6)	0.002 (5)	-0.009 (5)	-0.012 (5)
O21'	0.032 (5)	0.013 (6)	0.030 (6)	0.002 (5)	-0.009 (5)	-0.012 (5)
O22	0.045 (6)	0.042 (6)	0.029 (8)	-0.030 (5)	0.000	0.000
O22'	0.045 (6)	0.042 (6)	0.029 (8)	-0.030 (5)	0.000	0.000
O23	0.045 (6)	0.021 (6)	0.011 (5)	0.003 (5)	-0.011 (4)	0.006 (4)
O23'	0.045 (6)	0.021 (6)	0.011 (5)	0.003 (5)	-0.011 (4)	0.006 (4)
O24	0.020 (2)	0.032 (3)	0.022 (3)	0.012 (2)	-0.006 (3)	-0.003 (3)

Geometric parameters (Å, °)

Eu1—O21 ⁱ	2.217 (18)	Si1—O13	1.615 (5)
Eu1—O21 ⁱⁱ	2.344 (13)	P1—O11	1.514 (5)
Eu1—O23 ⁱⁱⁱ	2.309 (15)	P1—O12	1.523 (5)
Eu1—O23 ^{iv}	2.240 (12)	P1—O13	1.577 (5)
Eu1—O14 ^v	2.267 (5)	P1—O14	1.504 (5)
Eu1—O12 ^{vi}	2.349 (4)	P2—O21	1.476 (18)
Eu1—O11 ^{vii}	2.360 (4)	P2—O21'	1.496 (15)
Eu1—O12	2.451 (5)	P2—O22	1.536 (5)
Eu1—O11	2.544 (5)	P2—O22'	1.547 (5)
Si1—O24	1.593 (6)	P2—O23	1.520 (14)
Si1—O24 ^{viii}	1.593 (6)	P2—O23'	1.436 (12)
Si1—O13 ^{ix}	1.615 (5)	P2—O24	1.568 (5)
O21 ⁱ —Eu1—O14 ⁱⁱⁱ	82.2 (5)	O21 ⁱⁱ —Eu1—O11	149.4 (4)
O23 ⁱⁱⁱ —Eu1—O14 ⁱⁱⁱ	169.9 (4)	O12—Eu1—O11	57.32 (14)

O21 ⁱ —Eu1—O23 ⁱⁱ	87.6 (5)	O24—Si1—O24 ^{vi}	103.6 (5)
O14 ⁱⁱⁱ —Eu1—O23 ⁱⁱ	169.7 (4)	O24—Si1—O13 ^{vi}	112.5 (3)
O21 ⁱ —Eu1—O12 ^{iv}	78.4 (5)	O24 ^{vi} —Si1—O13 ^{vi}	111.4 (3)
O23 ⁱⁱ —Eu1—O12 ^{iv}	82.1 (4)	O24—Si1—O13	111.4 (3)
O14 ⁱⁱⁱ —Eu1—O12 ^{iv}	88.8 (2)	O24 ^{vi} —Si1—O13	112.5 (3)
O23 ⁱⁱ —Eu1—O12 ^{iv}	88.0 (5)	O13 ^{vi} —Si1—O13	105.6 (4)
O21 ⁱ —Eu1—O11 ^v	87.9 (5)	O14—P1—O11	115.4 (3)
O23 ⁱⁱ —Eu1—O11 ^v	96.4 (4)	O14—P1—O12	114.6 (3)
O14 ⁱⁱⁱ —Eu1—O11 ^v	93.5 (2)	O11—P1—O12	104.2 (3)
O23 ⁱⁱ —Eu1—O11 ^v	87.4 (5)	O14—P1—O13	107.8 (3)
O12 ^{iv} —Eu1—O11 ^v	165.72 (15)	O11—P1—O13	107.5 (3)
O14 ⁱⁱⁱ —Eu1—O21 ^{ri}	95.7 (4)	O12—P1—O13	106.8 (3)
O12 ^{iv} —Eu1—O21 ^{ri}	83.9 (4)	O21—P2—O23	116.4 (8)
O11 ^v —Eu1—O21 ^{ri}	81.9 (4)	O21—P2—O22	108.9 (10)
O21 ⁱ —Eu1—O12	156.9 (5)	O23—P2—O22	108.8 (11)
O23 ⁱⁱ —Eu1—O12	83.2 (4)	O21—P2—O24	110.7 (8)
O14 ⁱⁱⁱ —Eu1—O12	98.71 (18)	O23—P2—O24	109.6 (8)
O23 ⁱⁱ —Eu1—O12	91.1 (4)	O22—P2—O24	101.5 (2)
O12 ^{iv} —Eu1—O12	124.68 (12)	O23'—P2—O22'	109.0 (9)
O11 ^v —Eu1—O12	68.94 (15)	O21'—P2—O22'	109.7 (9)
O21 ^{ri} —Eu1—O12	148.0 (4)	O23'—P2—O24	108.4 (6)
O21 ⁱ —Eu1—O11	145.8 (5)	O23'—P2—O21'	118.1 (7)
O23 ⁱⁱ —Eu1—O11	78.3 (4)	O21'—P2—O24	108.4 (6)
O14 ⁱⁱⁱ —Eu1—O11	94.34 (18)	O22'—P2—O24	102.2 (2)
O23 ⁱⁱ —Eu1—O11	93.4 (4)	P2 ^{vii} —O22—P2	158 (2)
O12 ^{iv} —Eu1—O11	67.52 (15)	P2—O22'—P2 ^{vii}	154.1 (16)
O11 ^v —Eu1—O11	126.26 (12)		

Symmetry codes: (i) $-x+1/2, y+1/2, -z+2$; (ii) $-x+1/2, y+1/2, -z+3$; (iii) $x, y, z-1$; (iv) $x+1/2, -y+1/2, -z+2$; (v) $x-1/2, -y+1/2, -z+2$; (vi) $-x, -y, z$; (vii) $-x+1, -y, z$.